Quantum capacitance and spin susceptibility of HgTe quantum wells

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Outline

- Introduction & Motivation
 - topological insulators: more than just the edge states!
 - our model system: HgTe/CdTe quantum well
- Theoretical method
 - band structure from BHZ model Hamiltonian
 - calculate thermodynamic DOS, spin susceptibility, ...
- Results
 - importance of virtual inter-band processes
 - distinct physical properties of topological regime
- Conclusions







Introduction & Motivation









Electronic structure of crystalline solids

- atomic levels broaden into bands in solid material
 - character of bands reflects that of atomic orbitals
- (anti-)bonding levels \rightarrow (conduction) valence bands



Ordinary vs. topological insulator (TI)

- certain materials exist where order of bonding and anti-bonding bands is reversed: inverted bands
 - closing of gap required to go from normal type into the inverted situation: topologically distinct systems!

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• gapless states emerge at the surface of a topological material (due to symmetry!)

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www.scholarpedia.org/article/Topological_insulators

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2D TI "fruitfly system": HgTe quantum well

- adjust quantum-well width to tune between the normal & inverted regimes (bulk HgTe inverted!)
- helical edge states in topological regime (Kramers degeneracy!) give rise to quantum spin Hall effect

Kane & Mele, PRL (2005)

Bernevig, Hughes & Zhang, Science (2006) König et al., Science (2007); Roth et al., Science (2009), Brüne et al., Nat Phys (2012)



Explore Schrödinger-Dirac-TI continuum

- HgTe/CdTe system facilitates controlled access to transitions between these three model systems!
- single-particle eigenstates have a pseudo-spin texture
 - band mixing leads to unusual
 charge-response properties
 Jürgens, Michetti & Trauzettel, PRB (2014)
- Topological order affecting ^B collective-electron response properties?? Measurable!!





Bernevig, Hughes & Zhang, Science (2006)







Theoretical approach to studying the collective properties of 2D electrons in the HgTe/CdTe quantum-well system









Effective four-band (BHZ) model

- relevant physics involves states near the band gap
 - $-\Gamma_6$ (*j*=1/2): conduction band in normal regime
 - Γ_8 (*j*=3/2): heavy (*m_j*=±3/2) and light (*m_j*=±1/2) holes
 - hybridised Γ_6 & light-hole Γ_8 states form En subbands
- effective 4-band description for 2D E1/H1bands:



Many-particle properties of interest

- thermodynamic density of states: $D_{\rm T} \equiv \partial n / \partial \mu$
 - renormalised by Coulomb interactions (Fock term)
 - intra- and inter-band contributions + 2D form factor

$$\Sigma_{k\pm}^{(s)} = -2\pi C \int \frac{d^2 k'}{(2\pi)^2} n_{\rm F} \left(E_{\mathbf{k}'\pm}^{(s)} \right) \int dz \int dz' \; \frac{e^{-|\mathbf{k}-\mathbf{k}'||z-z'|}}{|\mathbf{k}-\mathbf{k}'|} \left[\psi_{\mathbf{k}'\pm}^{(s)}(z)^{\dagger} \cdot \psi_{\mathbf{k}+}^{(s)}(z) \right] \left[\psi_{\mathbf{k}+}^{(s)}(z')^{\dagger} \cdot \psi_{\mathbf{k}'\pm}^{(s)}(z') \right]$$

• spin susceptibility:

$$\chi_{ij}(\mathbf{R}, z; \mathbf{R}', z') = \lim_{\eta \to 0^+} \left\{ -\frac{i}{\hbar} \int_0^\infty dt \ e^{-\eta t} \langle [S_i(\mathbf{R}, z; t), S_j(\mathbf{R}', z'; 0)] \rangle \right\}$$

- collective spin response of many-electron system

$$\chi_{ij}(\gamma;\mathbf{q};z,z') = \sum_{\alpha,\beta,s,s'} \int \frac{d^2k}{(2\pi)^2} \, \mathscr{W}^{(s,s')}_{ij(\mathbf{k},\mathbf{k}+\mathbf{q},\alpha,\beta)}(\gamma;z,z') \frac{n_{\mathrm{F}}(E^{(s)}_{\mathbf{k}\alpha}) - n_{\mathrm{F}}(E^{(s')}_{\mathbf{k}+\mathbf{q}\beta})}{E^{(s)}_{\mathbf{k}\alpha} - E^{(s')}_{\mathbf{k}+\mathbf{q}\beta} + i\hbar\eta} \overset{(s,s')}{\underbrace{\mathcal{W}^{(s,s')}_{ij(\mathbf{k},\mathbf{k}+\mathbf{q},\alpha,\beta)}(\gamma;z,z')} = \left[\psi^{(s)}_{\mathbf{k}\alpha}(z)\right]^{\dagger} \cdot \left[\hat{S}_{i}(\gamma)\,\psi^{(s')}_{\mathbf{k}+\mathbf{q}\beta}(z)\right] \left[\psi^{(s')}_{\mathbf{k}+\mathbf{q}\beta}(z')\right]^{\dagger} \cdot \left[\hat{S}_{j}(\gamma)\,\psi^{(s)}_{\mathbf{k}\alpha}(z')\right]} \overset{(s)}{\longrightarrow}$$

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k+q, s'

Relation to physical observables

• thermodynamic DOS: quantum capacitance

$$\frac{A}{C_{\rm tot}} = \frac{d}{\kappa\epsilon_0} + \frac{1}{e^2 D_{\rm T}}$$



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• spin susceptibility: carrier-mediated (RKKY) exchange interac. of localised magnetic impurities

$$H_{\mathrm{RKKY}}^{(\alpha\beta)} = -G^2 \sum_{i,j} I_i^{(\alpha)} I_j^{(\beta)} \chi_{ij} (\mathbf{R}_{\alpha}, \mathbf{R}_{\beta})$$

$$T_{\mathrm{C}}^{(\perp,\parallel)} = \frac{I(I+1)}{3} \frac{G^2}{k_{\mathrm{B}}} \frac{n_{\mathrm{imp}}}{d} |\bar{\chi}_{zz,xx}(\mathbf{q}=0)|$$

Results









Thermodynamic DOS

- normal regime: similar to ordinary 2D el. system
 in particular also tendency to negative compressibility!
- topological regime: different due to inter-band contribution, suppressed negative compressibility!



Implication for quantum capacitance

- inter-band exchange-renormalisation of thermodynamic DOS varies strongly through transition
- quantum capacitance heralds topological phase!

- in both magnitude and density dependence



Spin susceptibility: Undoped system

• vary gap parameter $\xi_M = M \cdot |B|/A^2 = -0.3, \dots, 0.3$



– finite at q = 0; independent of ξ_M in topological regime

• analytic result for static uniform spin susceptibility

$$\overline{\chi}_{xx,zz}^{(\text{int})}(\gamma;\mathbf{q}=0) = -\frac{\mathcal{C}_{x,z}^2(\gamma)}{16\pi|B|} \frac{1}{1+4\xi_{\rm M}\Theta(\xi_{\rm M})}$$









Susceptibility of electron-doped system

- sum of intrinsic & doping-dependent contributions
- complex dependence on parameters, density, ...
- unconventional 2DEG response
 - band-mixing effects are strong!



Application: Carrier-mediated magnetism

- mean-field: uniform Ising magnetisation ($\chi_{zz} \gg \chi_{xx}$)
- clear asymmetry between topological and normal regimes, in both un-doped and doped cases!
- magnons: magnetism (un-)stable in (un-)doped case



Application: Collective-electron g factor

• relate calculated paramagnetic spin susceptibility to Pauli susceptibility: yields collective g factor

$$\mathcal{H}_{\mathcal{B}} = g_* \,\mu_{\mathrm{B}} \sum_{j} \mathcal{B}_j \,\hat{S}_j \left(-\frac{2\kappa}{g_*}\right)$$
$$g_j = g_* \,\sqrt{4 \, \frac{\overline{\chi}_{jj}^{(\mathrm{dop})}(-2\kappa/g_*;q)}{\overline{\chi}_0(q)}}\Big|_{q=0}$$

 experimentally relevant measure for Zeeman splitting in a many-electron systems with spin-orbit coupling

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Kernreiter, Governale, UZ, PRL (2013)

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Spin response of helical edge states

- calculated spin susceptibility of helical edge states based on their quantum description Zhou et al. PRL (2008)
- derived collective 1D edge-electron g factors



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Conclusions

- comprehensive study of many-electron properties in HgTe quantum-well 2D electron system
- distinctive features in topological regime revealed
 - thermodynamic DOS: positive inter-band Fock term
 - intrinsic q = 0 spin susceptibility: no gap dependence
- considered physical implications
 - quantum capacitance/compressibility
 - carrier-mediated magnetism, effective g factor
- our study is focused on the HgTe quantum-well system, but conclusions valid more generally

Kernreiter, Governale, UZ & Hankiewicz, Phys. Rev. X 6, 021010 (2016) Kernreiter, Governale, UZ, Phys. Rev. B 93, 241304(R) (2016)

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